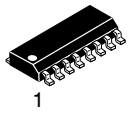
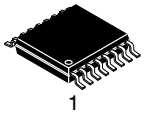
3-to-8 Line Decoder
MC74VHCT138A



SOIC−16
D SUFFIX
CASE 751B



TSSOP−16
DT SUFFIX
CASE 948F

The MC74VHCT138A is an advanced high speed CMOS 3−to−8 decoder fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

When the device is enabled, three Binary Select inputs (A0 − A2) determine which one of the outputs ($\overline{Y0}$ − $\overline{Y7}$) will go Low. When enable input E3 is held Low or either $\overline{E2}$ or $\overline{E1}$ is held High, decoding function is inhibited and all outputs go high. E3, $\overline{E2}$, and $\overline{E1}$ inputs are provided to ease cascade connection and for use as an address decoder for memory systems.

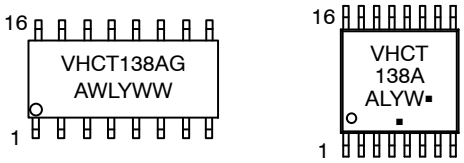
The VHCT inputs are compatible with TTL levels. This device can be used as a level converter for interfacing 3.3 V to 5.0 V, because they have full 5.0 V CMOS level output swings.

The VHCT138A input structures provide protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. The output structures also provide protection when V_{CC} = 0 V. These input and output structures help prevent device destruction caused by supply voltage − input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- High Speed: t_{PD} = 7.6 ns (Typ) at V_{CC} = 5.0 V
- Low Power Dissipation: I_{CC} = 4 μA (Max) at T_A = 25°C
- TTL−Compatible Inputs: V_{IL} = 0.8 V; V_{IH} = 2.0 V
- Power Down Protection Provided on Inputs and Outputs
- Balanced Propagation Delays
- Designed for 4.5 V to 5.5 V Operating Range
- Pin and Function Compatible with Other Standard Logic Families
- Latchup Performance Exceeds 300 mA
- ESD Performance:
  Human Body Model > 2000 V;
  Machine Model > 200 V
- Chip Complexity: 122 FETs or 30.5 Equivalent Gates
- These Devices are Pb−Free and are RoHS Compliant

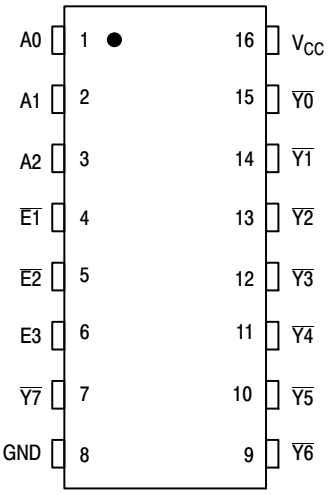
MARKING DIAGRAM



A	=	Assembly Location
WL, L	=	Wafer Lot
Y	=	Year
WW, W	=	Work Week
G or ▪	=	Pb−Free Package

(Note: Microdot may be in either location)

PIN ASSIGNMENT



ORDERING INFORMATION

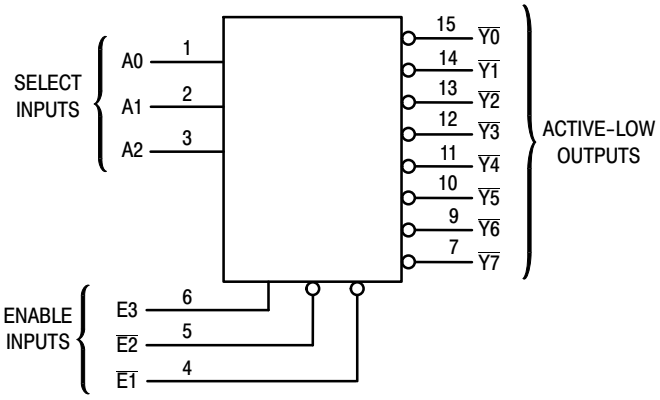
See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

FUNCTION TABLE

Inputs						Outputs							
E3	$\overline{E2}$	$\overline{E1}$	A2	A1	A0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y7
X	X	H	X	X	X	H	H	H	H	H	H	H	H
X	H	X	X	X	X	H	H	H	H	H	H	H	H
L	X	X	X	X	X	H	H	H	H	H	H	H	H
H	L	L	L	L	L	L	H	H	H	H	H	H	H
H	L	L	L	L	H	H	L	H	H	H	H	H	H
H	L	L	L	H	L	H	H	L	H	H	H	H	H
H	L	L	L	H	H	H	H	H	L	H	H	H	H
H	L	L	H	L	L	H	H	H	H	L	H	H	H
H	L	L	H	L	H	H	H	H	H	H	L	H	H
H	L	L	H	H	L	H	H	H	H	H	H	L	H
H	L	L	H	H	H	H	H	H	H	H	H	H	L

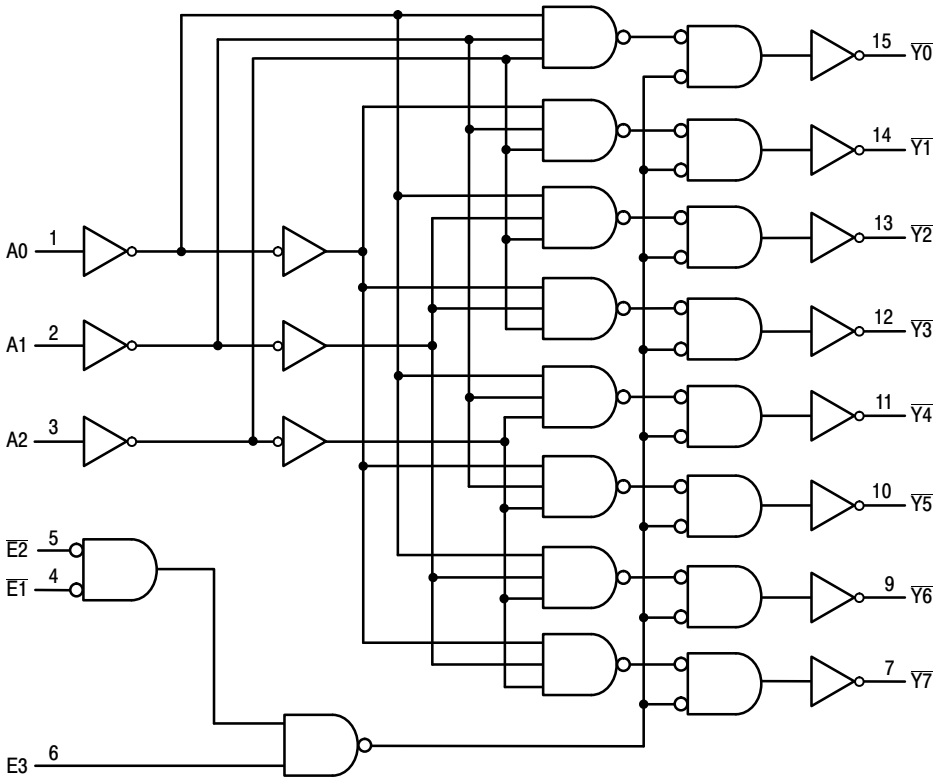
H = high level (steady state); L = low level (steady state);
X = don't care

LOGIC DIAGRAM

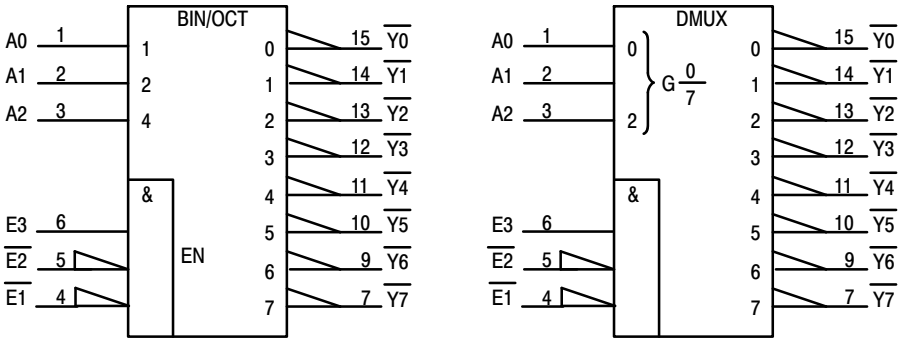


MC74VHCT138A

EXPANDED LOGIC DIAGRAM



IEC LOGIC DIAGRAM



MAXIMUM RATINGS

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		– 0.5 to + 7.0	V
V_{in}	DC Input Voltage		– 0.5 to + 7.0	V
V_{out}	DC Output Voltage	V_{CC} = 0 High or Low State	– 0.5 to + 7.0 – 0.5 to V_{CC} + 0.5	V
I_{IK}	Input Diode Current		– 20	mA
I_{OK}	Output Diode Current (V_{OUT} < GND; V_{OUT} > V_{CC})		±20	mA
I_{out}	DC Output Current, per Pin		±25	mA
I_{CC}	DC Supply Current, V_{CC} and GND Pins		±75	mA
P_D	Power Dissipation in Still Air,	SOIC Packages† TSSOP Package†	500 450	mW
T_{stg}	Storage Temperature		– 65 to + 150	°C

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

†Derating – SOIC Packages: – 7 mW/°C from 65° to 125°C
TSSOP Package: – 6.1 mW/°C from 65° to 125°C

This device contains protection circuitry to guard against damage due to high static voltages or electric fields. However, precautions must be taken to avoid applications of any voltage higher than maximum rated voltages to this high–impedance circuit. For proper operation, V_{in} and V_{out} should be constrained to the range GND ≤ (V_{in} or V_{out}) ≤ V_{CC}.

Unused inputs must always be tied to an appropriate logic voltage level (e.g., either GND or V_{CC}). Unused outputs must be left open.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Max	Unit
V_{CC}	DC Supply Voltage		3.0	5.5	V
V_{in}	DC Input Voltage		0	5.5	V
V_{out}	DC Output Voltage	V_{CC} = 0 High or Low State	0 0	5.5 V_{CC}	V
T_A	Operating Temperature		– 55	+ 125	°C
t_r, t_f	Input Rise and Fall Time	V_{CC} =5.0V ±0.5V	0	20	ns/V

The θ_{JA} of the package is equal to 1/Derating. Higher junction temperatures may affect the expected lifetime of the device per the table and figure below.

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

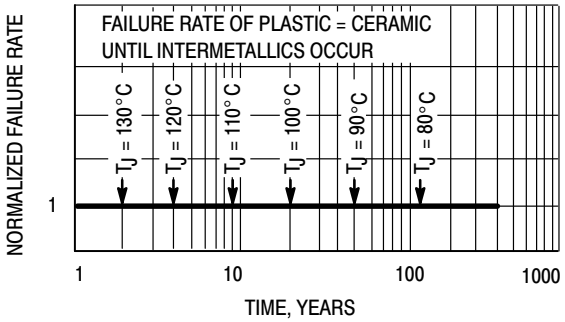


Figure 1. Failure Rate vs. Time Junction Temperature

DC ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Test Conditions	V_{CC} (V)	T_A = 25°C			$T_A \le$ 85°C		$T_A \le$ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
V_{IH}	Minimum High−Level Input Voltage		3.0 4.5 5.5	1.4 2.0 2.0			1.4 2.0 2.0		1.4 2.0 2.0		V
V_{IL}	Maximum Low−Level Input Voltage		3.0 4.5 5.5			0.53 0.8 0.8		0.53 0.8 0.8		0.53 0.8 0.8	V
V_{OH}	Minimum High−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	V_{IN} = V_{IH} or V_{IL} I_{OH} = −50 μA	3.0 4.5	2.9 4.4	3.0 4.5		2.9 4.4		2.9 4.4		V
		V_{IN} = V_{IH} or V_{IL} I_{OH} = −4 mA I_{OH} = −8 mA	3.0 4.5	2.58 3.94			2.48 3.80		2.34 3.66		V
V_{OL}	Maximum Low−Level Output Voltage V_{IN} = V_{IH} or V_{IL}	V_{IN} = V_{IH} or V_{IL} I_{OL} = 50 μA	3.0 4.5		0.0 0.0	0.1 0.1		0.1 0.1		0.1 0.1	V
		V_{IN} = V_{IH} or V_{IL} I_{OL} = 4 mA I_{OL} = 8 mA	3.0 4.5			0.36 0.36		0.44 0.44		0.52 0.52	V
I_{IN}	Maximum Input Leakage Current	V_{IN} = 5.5 V or GND	0 to 5.5			±0.1		±1.0		±1.0	μA
I_{CC}	Maximum Quiescent Supply Current	V_{IN} = V_{CC} or GND	5.5			4.0		40.0		40.0	μA
I_{CCT}	Quiescent Supply Current	V_{IN} = 3.4 V	5.5			1.35		1.50		1.50	mA
I_{OPD}	Output Leakage Current	V_{OUT} = 5.5 V	0.0			0.5		5.0		5.0	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3.0ns)

Symbol	Parameter	Test Conditions		T_A = 25°C			T_A = ≤ 85°C		$T_A \le$ 125°C		Unit
				Min	Typ	Max	Min	Max	Min	Max	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input A to Y	V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF		9.5 10.8	14.5 15.5	1.0 1.0	16.0 17.0	1.0 1.0	16.0 17.0	ns
		V_{CC} = 5.0 ± 0.5V	C_L = 15pF C_L = 50pF		7.6 8.1	10.4 11.4	1.0 1.0	12.0 13.0	1.0 1.0	12.0 13.0	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input E3 to Y	V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF		9.7 9.5	13.0 14.0	1.0 1.0	14.5 15.5	1.0 1.0	14.5 15.5	ns
		V_{CC} = 5.0 ± 0.5V	C_L = 15pF C_L = 50pF		6.6 7.1	9.1 10.1	1.0 1.0	10.5 11.5	1.0 1.0	10.5 11.5	
t_{PLH}, t_{PHL}	Maximum Propagation Delay, Input $\overline{E1}$ or $\overline{E2}$ to Y	V_{CC} = 3.3 ± 0.3V	C_L = 15pF C_L = 50pF		10.1 9.9	14.0 15.0	1.0 1.0	15.5 16.5	1.0 1.0	15.5 16.5	ns
		V_{CC} = 5.0 ± 0.5V	C_L = 15pF C_L = 50pF		7.0 7.5	9.6 10.6	1.0 1.0	11.0 12.0	1.0 1.0	11.0 12.0	
C_{IN}	Maximum Input Capacitance				4	10		10		10	pF

		Typical @ 25°C, V_{CC} = 5.0V	
C_{PD}	Power Dissipation Capacitance (Note 1)	49	pF

1. C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: $I_{CC(OPR)}$ = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no−load dynamic power consumption; P_D = C_{PD} • V_{CC}^2 • f_{in} + I_{CC} • V_{CC}.

SWITCHING WAVEFORMS

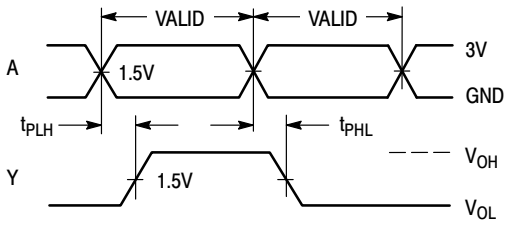


Figure 2.

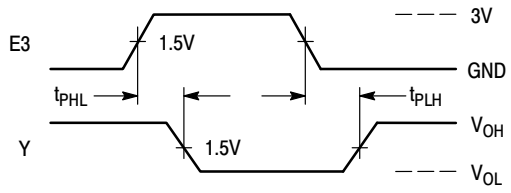


Figure 3.

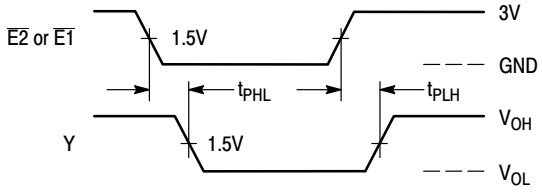
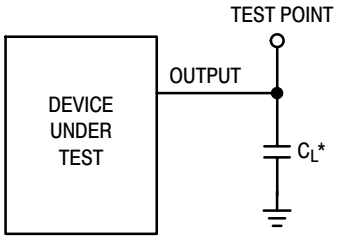


Figure 4.



*Includes all probe and jig capacitance

Figure 5. Test Circuit

ORDERING INFORMATION

Device	Package	Shipping†
MC74VHCT138ADR2G	SOIC−16 (Pb−Free)	2500 Tape & Reel
MC74VHCT138ADTRG	TSSOP−16*	2500 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.
*This package is inherently Pb−Free.

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales